



April 2000

**QFET™**

## FQPF2N60

### 600V N-Channel MOSFET

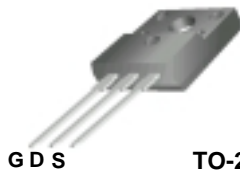
#### General Description

These N-Channel enhancement mode power field effect transistors are produced using Corise Semiconductor's proprietary, planar stripe, DMOS technology.

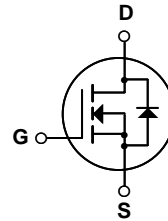
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply.

#### Features

- 1.6A, 600V,  $R_{DS(on)} = 4.7\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 9.0 nC)
- Low Crss ( typical 5.0 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



**TO-220F**  
FQPF Series



#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FQPF2N60	Units
V <sub>DSS</sub>	Drain-Source Voltage	600	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	1.6	A
		1.0	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	6.4	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	140	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	1.6	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	28	W
		0.22	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

#### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	--	4.46	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.4	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.8\text{ A}$	--	3.7	4.7	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 0.8\text{ A}$ (Note 4)	--	2.0	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	270	350	pF
$C_{oss}$	Output Capacitance		--	40	50	pF
$C_{rss}$	Reverse Transfer Capacitance		--	5	7	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 2.4\text{ A},$ $R_G = 25\ \Omega$	--	10	30	ns	
$t_r$	Turn-On Rise Time		--	25	60	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	20	50	ns
$t_f$	Turn-Off Fall Time		--	25	60	ns	
$Q_g$	Total Gate Charge		$V_{DS} = 480\text{ V}, I_D = 2.4\text{ A},$ $V_{GS} = 10\text{ V}$	--	9.0	11	nC
$Q_{gs}$	Gate-Source Charge	(Note 4, 5)	--	1.6	--	nC	
$Q_{gd}$	Gate-Drain Charge		--	4.3	--	nC	

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	1.6	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	6.4	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.6\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 2.4\text{ A},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$	--	180	--	ns
$Q_{rr}$	Reverse Recovery Charge	(Note 4)	--	0.72	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 100\text{ mH}, I_{AS} = 1.6\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 2.4\text{ A}, dI/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

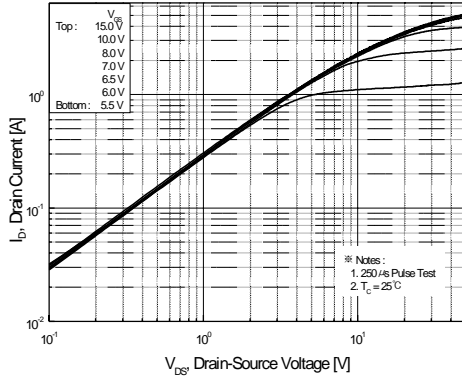


Figure 1. On-Region Characteristics

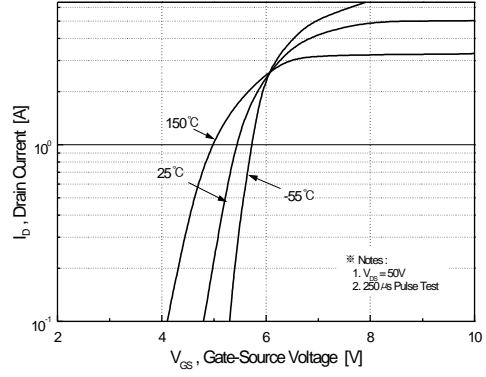


Figure 2. Transfer Characteristics

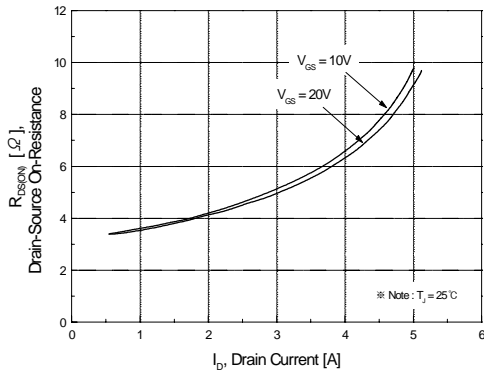


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

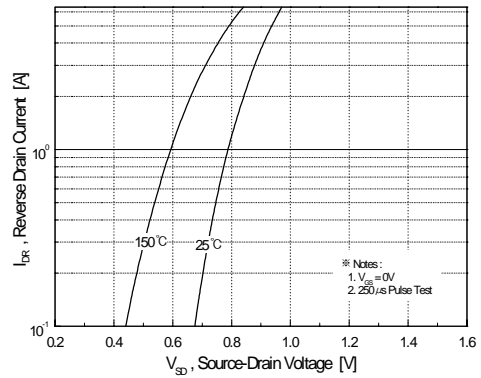


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

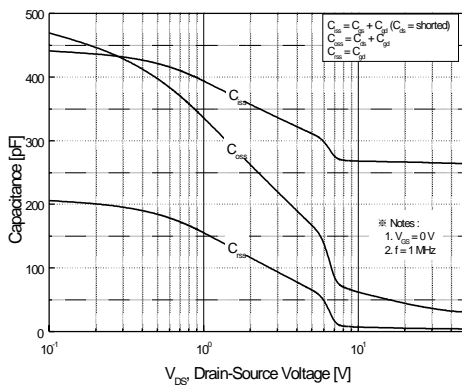


Figure 5. Capacitance Characteristics

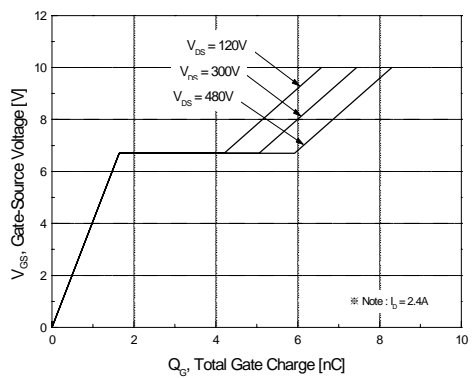
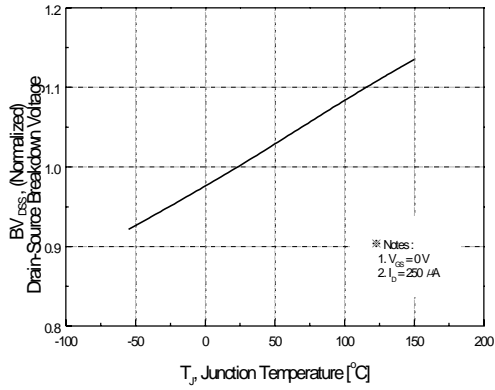
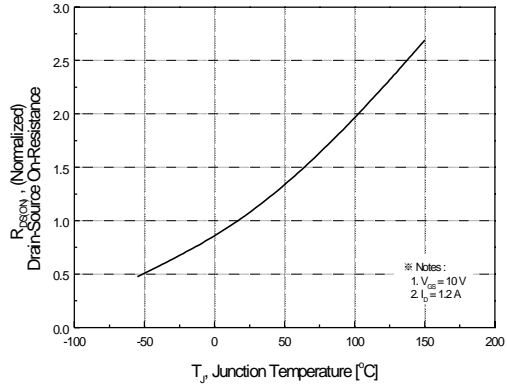


Figure 6. Gate Charge Characteristics

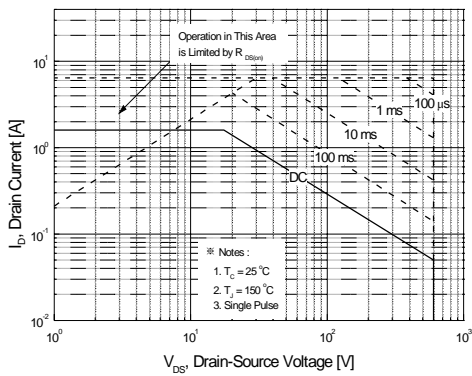
## Typical Characteristics



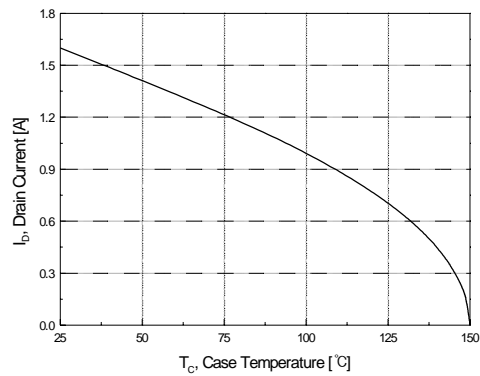
**Figure 7. Breakdown Voltage Variation vs. Temperature**



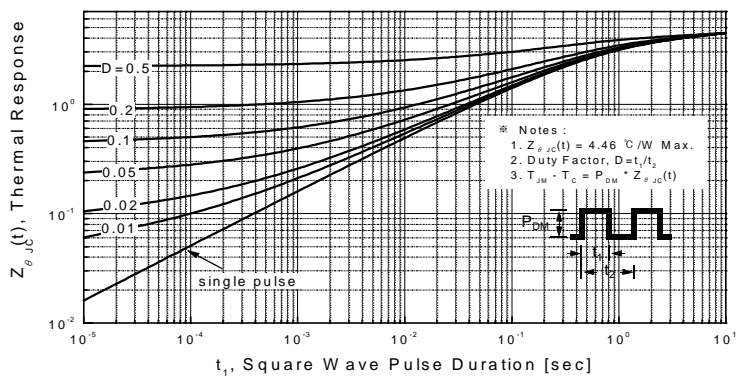
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**

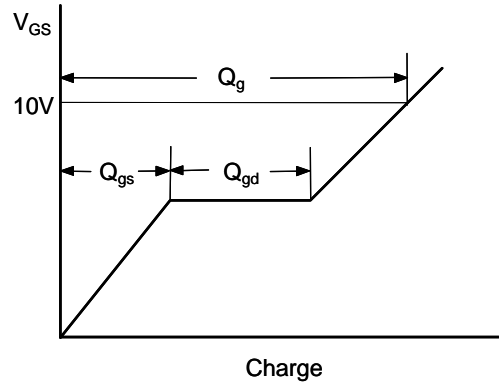
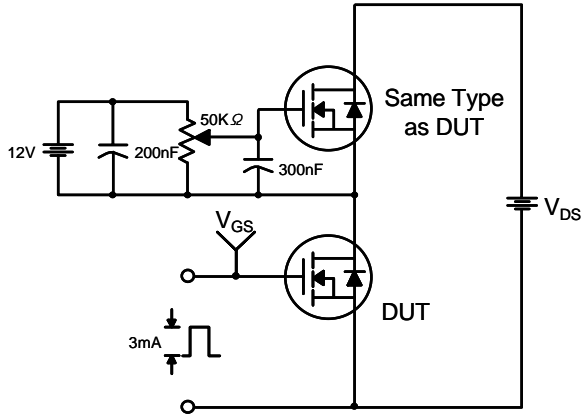


**Figure 10. Maximum Drain Current vs. Case Temperature**

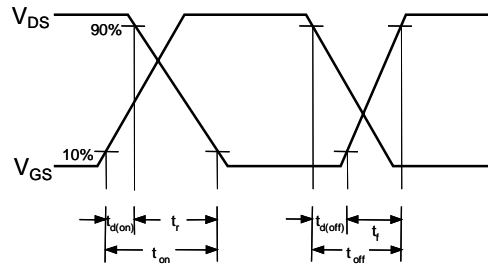
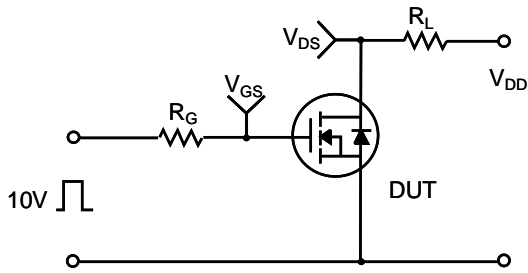


**Figure 11. Transient Thermal Response Curve**

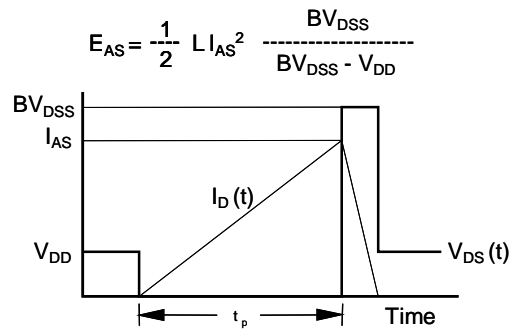
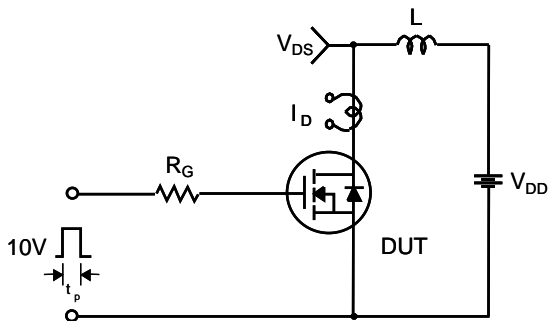
Gate Charge Test Circuit & Waveform

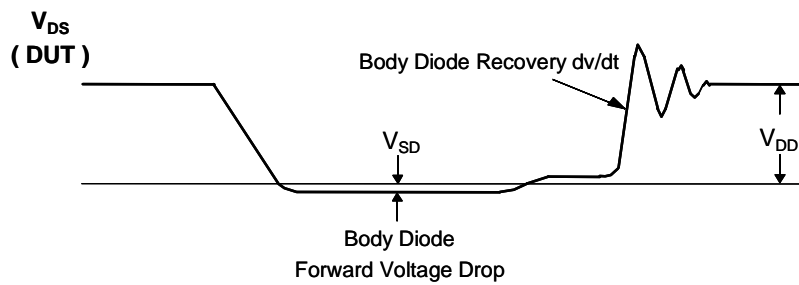
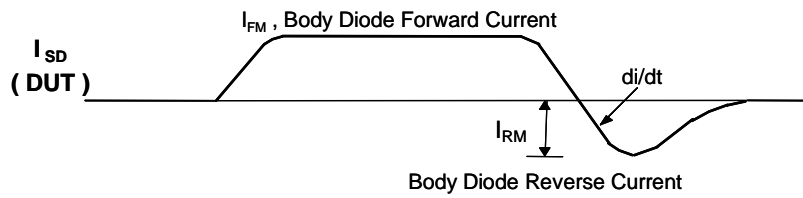
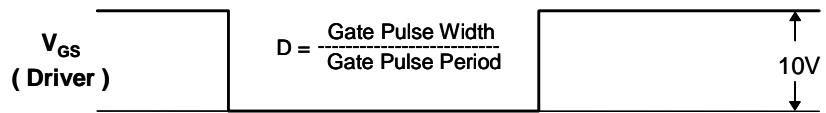
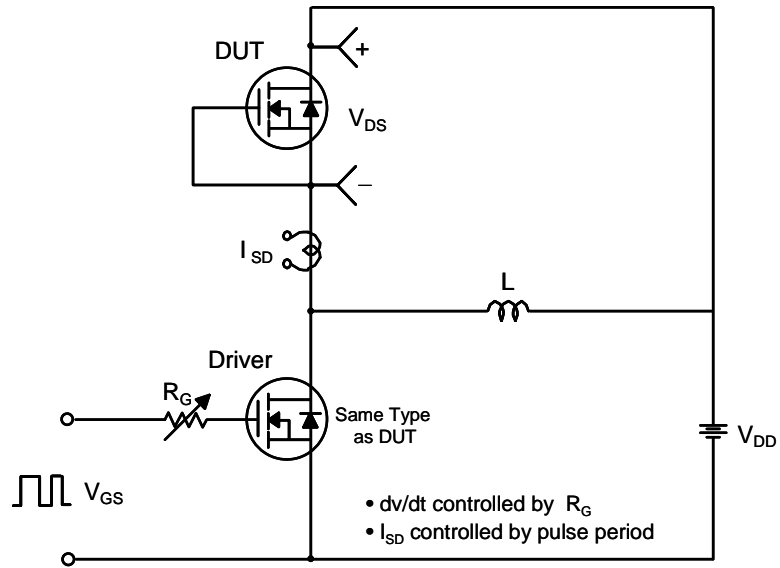


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms





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